

APPENDIX A
"CLEAN" VERSION OF EACH PARAGRAPH/SECTION/CLAIM
37 C.F.R. § 1.121(b)(ii) AND (c)(i)

CLAIMS (with indication of amended or new):

1. (Twice Amended) A process of connecting semiconductor die to a substrate having a top surface,

said process comprising the steps of:

providing a thin, flexible, heat curable, polyimide, insulative film which is of a first area;

laying said thin flexible film on a thin semiconductor wafer of a second area, said semiconductor wafer being provided with a plurality of spaced apart semiconductor die, each of said semiconductor die having a respective third area which is substantially less than said first area;

D¹ preheating said semiconductor wafer and said thin flexible film to partially cure said thin flexible film, thereby forming adhesion between said thin flexible film and said semiconductor wafer;

thereafter simultaneously singulating both said thin flexible film and said plurality of identical semiconductor die to form individual elements;

heating said substrate;

thereafter placing at least one of said singulated semiconductor die on the top surface of said heated substrate with the thin flexible film on said die pressed against said top surface and adhered thereto; and

thereafter heating said semiconductor die and said substrate to a curing temperature to fully cure said thin flexible film to firmly adhere said semiconductor die to said substrate.

12. (Twice Amended) A method of manufacturing a semiconductor device comprising the steps of:

D² providing a wafer with a plurality of spaced apart semiconductor elements;

laying a thin, flexible, polyimide, insulative film, which is separate from said wafer, and said wafer atop one another to form a film/wafer structure;

preheating said film/wafer structure to partially cure said thin flexible film, thereby forming adhesion between said thin flexible film and said wafer;

singulating said film/wafer structure with said partially cured thin flexible film, thereby forming a plurality of individual semiconductor dies;

heating said substrate;

placing at least one individual semiconductor die with said partially cured thin flexible film, which faces a substrate, on the said heated substrate; and

applying heat to fully cure said thin flexible film, thereby bonding said individual semiconductor die with said substrate.

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D2